

## **Schottky Barrier Rectifiers**

Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

- \* Low Forward Voltage.
- \* Low Switching noise.
- \* High Current Capacity
- \* Guarantee Reverse Avalanche.
- \* Guard-Ring for Stress Protection.
- \* Low Power Loss & High efficiency.
- \* 150 Operating Junction Temperature
- \* Low Stored Charge Majority Carrier Conduction.
- \* Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

## **MAXIMUM RATINGS**

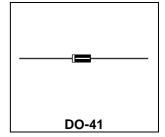
Characteristic	Symbol	1N5817	1N5818	1N5819	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	20	30	40	V
RMS Reverse Voltage	VR <sub>(RMS)</sub>	14	21	28	V
Average Rectifier Forward Current	Io	1.0		Α	
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-wave, single phase,60Hz)	I <sub>FSM</sub>	25		А	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150			

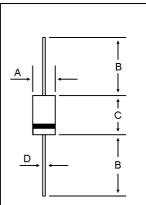
## **ELECTRIAL CHARACTERISTICS**

Characteristic	Symbol	1N5817	1N5818	1N5819	Unit
Maximum Instantaneous Forward Voltage (I <sub>F</sub> =1.0 Amp) (I <sub>F</sub> =3.0 Amp)	V <sub>F</sub>	0.450 0.750	0.550 0.875	0.600 0.900	V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25$ ) (Rated DC Voltage, $T_C = 125$ )	I <sub>R</sub>	0.5 20		mA	
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	СР	90 80		pF	

## SCHOTTKY BARRIER RECTIFIERS

1.0 AMPERES 20-40 VOLTS





DIM	MILLIMETERS			
ווווט	MIN	MAX		
Α	2.00	2.70		
В	25.40			
С	4.10	5.20		
D	0.70	0.90		

CASE---

Transfer molded plastic

POLARITY---Cathode indicated polarity band

